N-Channel 80-V (D-S) MOSFET

Key Features:

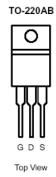
- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

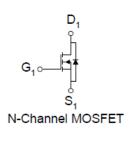
Typical	Appl	licatior	IS:
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- White LED boost converters
- · Automotive Systems
- Industrial DC/DC Conversion Circuits

PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I _D (A)		
80	5.5 @ V _{GS} = 10V	90a		
	$6.5 @ V_{GS} = 4.5V$	90		







ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			80	V		
Gate-Source Voltage			±20	V		
Continuous Drain Current a	T _A =25°C	I_D	90 ^a			
Pulsed Drain Current ^b			350	Α		
Continuous Source Current (Diode Conduction) a	I _S	120				
Power Dissipation ^a	T _A =25°C	P_{D}	300	W		
Operating Junction and Storage Temperature Range			-55 to 175	°C		

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient ^a	t <= 10 sec	D	62.5	°C/W		
IMAXIIIIUIII JUIICUOII-to-AIIIbleIIt	Steady State	$R_{\theta JA}$	0.5			

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Notes

- a. Package Limited
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

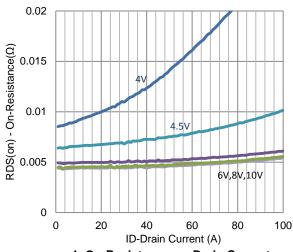
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current		$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Brain Gunerit	I _{DSS}	$V_{DS} = 64 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	45			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 45 \text{ A}$			5.5	mΩ	
Dialii-Source On-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 44 \text{ A}$			6.5	11122	
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 45 \text{ A}$		22		S	
Diode Forward Voltage	V_{SD}	$I_{S} = 60 \text{ A}, V_{GS} = 0 \text{ V}$		0.9		V	
		Dynamic					
Total Gate Charge	Q_g			112			
Gate-Source Charge	Q_{gs}	$V_{DS} = 40 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 20 \text{ A}$		23		nC	
Gate-Drain Charge	Q_gd			76			
Turn-On Delay Time	t _{d(on)}			25			
Rise Time	t _r	$V_{DS} = 40 \text{ V}, R_L = 2 \Omega, I_D = 20 \text{ A},$		56		nc	
Turn-Off Delay Time	t _{d(off)}	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		360		ns	
Fall Time	t _f			122			
Input Capacitance	C _{iss}			10609			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		989		pF	
Reverse Transfer Capacitance	C_{rss}			936			

Notes

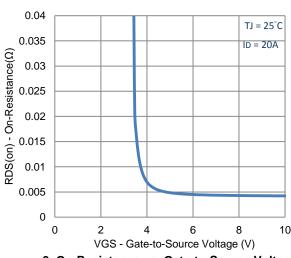
- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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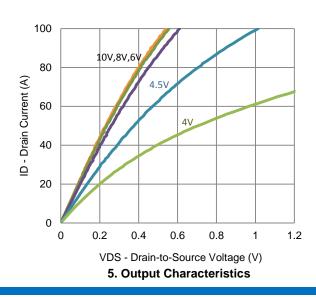
Typical Electrical Characteristics

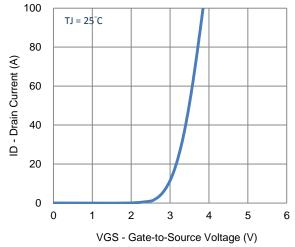


1. On-Resistance vs. Drain Current

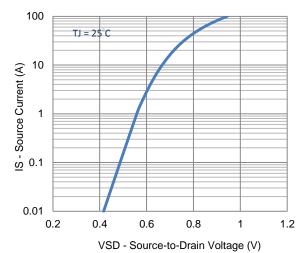


3. On-Resistance vs. Gate-to-Source Voltage

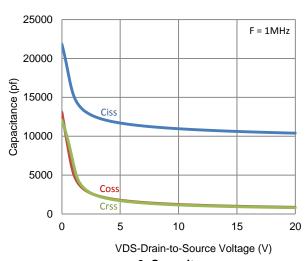




2. Transfer Characteristics

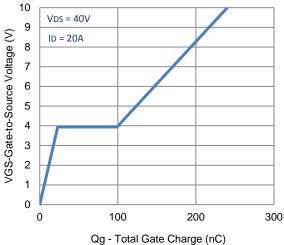


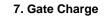
4. Drain-to-Source Forward Voltage

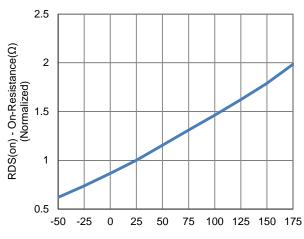


6. Capacitance

Typical Electrical Characteristics

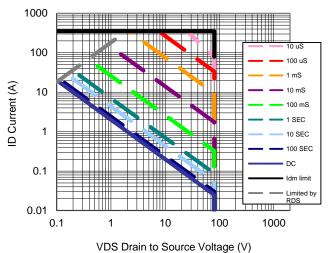




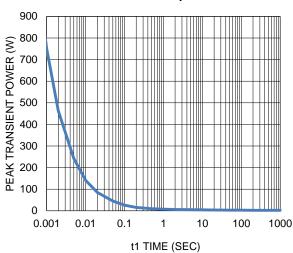


TJ -JunctionTemperature(°C)

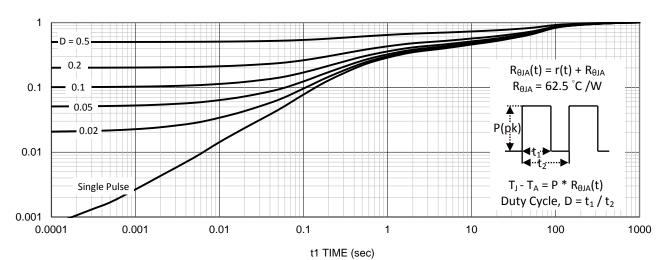




9. Safe Operating Area

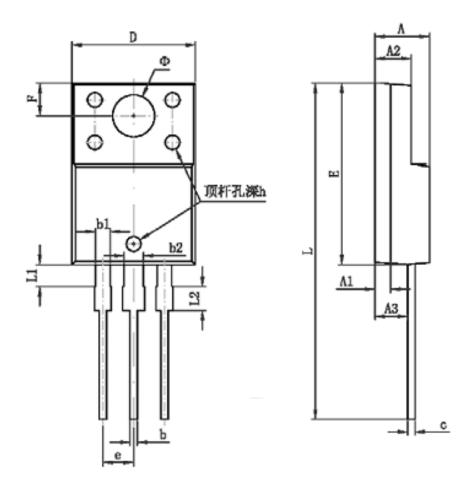


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



Symbol	Dimensions in Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	4.300	4.700	0.169	0.185	
A1	1.300	1.300 REF		REF	
A2	2.800	3.200	0.110	0.126	
A3	2.500	2.900	0.098	0.114	
b	0.500	0.750	0.020	0.030	
b1	1.100	1.350	0.043	0.053	
b2	1.500	1.750	0.059	0.069	
С	0.500	0.750	0.020	0.030	
D	9.960	10.360	0.392	0.408	
E	14.800	15.200	0.583	0.598	
e	2.540 TYP		0.100 TYP		
F	2.700 REF		0.106 REF		
Ф	3.500 REF		0.138 REF		
h	0.000	0.300	0.000	0.012	
L	28.000	28.400	1.102	1.118	
L1	1.700	1.900	0.067	0.075	
L2	1.900	2.100	0.075	0.083	